Preface

Interconnection Limits on XXI Century Gigascale Integration (GSI) p. 3

Power Supply Distribution and Other Wiring Issues for Deep-Submicron IC's p. 11

Multilevel Interconnection Technologies and Future Requirements for Logic Applications p. 29

Copper ULSI Interconnect Technology p. 39

Integration of Multi-Level Copper Metallization into a High-Performance Sub-0.25 [mu]m Technology p. 41

Scaling and Integration of High-Performance Interconnects p. 53

Sub-Quarter Micron Metallization Using Ionized Metal Plasma Technology p. 65

Barriers for Copper Interconnections p. 75

Materials and Devices for Silicon On-Chip Optical Interconnect p. 83

Texture Control and Electromigration Performance in Al-Based and Cu-Based Layered Interconnects p. 91

Al Dual Damascene Technology for Multilevel Interconnects p. 103

Crystallographic Texture and Phase Formation in Blanket Ti/TiN/AlCu Films p. 105

Microstructure and Lifetime Study of Al/Y Films p. 107

Investigation of the Homovalent Impurity in Aluminum to Form Alloys With Enhanced Interconnect Reliability p. 113

Simulators of Thin Film Deposition for Silicon Device Processing p. 119

Study of Factor and Interaction Effects During Programmed Rate Chemical Vapor Deposition of Aluminum p. 121

Monte Carlo Atomistic Simulation of Polycrystalline Aluminum Deposition p. 127

Comparison of the Electromigration Behavior of Al(MgCu) With Al(Cu) and Al(SiCu) p. 133

Imaging Spatial Variations in Resistance Along Interconnects p. 139

Debonding of Interfaces in Multilayer Interconnect Structures p. 141

Growth, Patterning and Microelectronic Applications of Epitaxial CobaltDisilicide p. 145

Improved Thermal Stability of Ultrathin CoSi[subscript 2] Layers by Oxygen Annealing p. 157

Nanopatterning of Thin CobaltDisilicide Layers by Local Oxidation p. 163

Thickness Effects in the Reaction of Cobalt With Silicon-Germanium Alloys p. 165

Silicide Technology in Deep Submicron Regime p. 171

Integration of NiSi Salicide for Deep Submicron CMOS Technologies p. 179

Morphology of NiSi Film on Si(100): Role of the Interface Strain p. 185

Formation and Thermal Stability of Nd[subscript 0.32]Y[subscript 0.68]Si[subscript 1.7] Layers Formed by Channeled Ion Beam Synthesis p. 191

Growth and Characterization of Self-Aligned Erbium Silicide on N-Type, (100) Oriented Silicon p. 197

Low-Temperature Formation of C54 TiSi[subscript 2] By-Passing the C49 Phase: Effect of Si Crystallinity, Metallic Impurities and Applications to 0.10 [mu]m CMOS p. 201

Mechanism of Narrow Line Effect in TiSi[subscript 2] Films on Highly As-Doped Diffusion Layers p. 207

C49-TiSi[subscript 2] Epitaxial Orientation Dependence of the C49-to-C54 Phase Transformation Rate p. 213
Kinetics of the C49-C54 Transformation in Patterned and Blanket TiSi\textsubscript{2} Films: A Comparison

A Suppression of the Phase Transition and Agglomeration of TiSi\textsubscript{2} by Addition of Zr Element

Selective Rapid Thermal Chemical Vapor Deposition of Titanium Silicide on Arsenic Implanted Silicon

The Control and Impact of Processing Ambient During RTP

New Approaches for Formation of Ultra-Thin PiSi Layers for Infrared Applications

Is Selective CVD an Improvement for the Titanium Silicide Process in Sub-Quarter Micron Technology? A Phase Formation Study Using X-ray Diffraction

A Novel Low-Temperature Self-Aligned Ti Silicide Technology for Sub-0.18 [mu]m CMOS Devices

Process Design and Integration of Salicide and Source/Drain Process Modules for Improved Device Performance

A Study of Transistor Optimization in a 0.25 Micron CMOS Flow Using S/D and Silicide Process Modules and Their Interactions

Optimization of Ti and Co Self-Aligned Silicide RTP for 0.10 [mu]m CMOS

Capacitance-Voltage, Current Voltage, and Thermal Stability of Copper Alloyed with Aluminum or Magnesium

Properties of Cu\textsubscript{3}Ge Films for Contacts to Si and SiGe and Cu Metallization

Copper Electroplating for Damascene ULSI Interconnects

Homogenization of the Bilayers of Cu-Al Alloy and Pure Copper to Produce Cu-0.3 at.% Al Alloy Films

Extendibility of Cu Damascene to 0.1 [mu]m Wide Interconnections

Microstructure and Texture of Electroplated Copper in Damascene Structures

Finite Element Modelling for Interconnect Materials and Structures

MOCVD of Copper From the Solution of New and Liquid Precursor (hfac)Cu(1-pentene)

Ambient Dependence of Agglomeration Stability of Cu/Ta Films

Sensitive Analysis of Deposition Chemistry of Cu From (hfac)Cu(tmvs) Using Well-Characterized Test Structure

Solution Delivery for Copper CVD Using Cu[hfac]\textsubscript{2} Reduction

Effect of Oxygen on the Degradation of Ti-Si-N Diffusion Barriers in Cu Metallization


Atomic Layer Deposition of TiN Thin Films by Sequential Introduction of Ti Precursor and NH[subscript 3]

The Effect of Impurities in TiN Film When Used as MOS Gate Electrodes

Formation of TiSi[subscript 2] Thin Films From Chemical Vapor Deposition Using Ti[subscript 4]

Pre-Treatment Effect on Aluminum Thin Films Deposition From CVD Using Dimethylethylamine Alane

Etching of Platinum Thin Films by High Density Ar/Cl[subscript 2]/HBr Plasma

Kelvin Test Structure Modelling of Metal-Silicide-Silicon Contacts

A Main Factor Determining the Uniform Step Coverage in Chemical Vapor Deposition
The Influence of Capping Layer Type on Cobalt Salicide Formation in Films and Narrow Lines

Effect of Lateral Dimension Scaling on Thermal Stability of Thin CoSi$_2$ Layers on Polysilicon Implanted With Si

Doping Influence on TiSi$_2$ C49-C54 Conversion Kinetics by Micro-Raman Spectroscopy

Theoretical Reactor Design from the Simple Tubular Reactor Analysis for WSix CVD Process

Analysis of Copper and Low-K Dielectric Interconnect System for 0.18-μm Technology

Ion Beam Induced Metallorganic Chemical Vapor Deposition of Titanium Nitride Films as a Diffusion Barrier Between Cu and Si

TiN Diffusion Barrier Formation by Pulsed Source Chemical Vapor Deposition Method

Diffusion Barrier Properties of the TiN Films Prepared by ECR PECVD Method

Process Windows of Titanium, Cobalt and Nickel Silicide in Deep Submicron Poly-Si Lines

Effects of Boron on Diffusion Barrier Characteristics of PECVD W-B-N Films

Characterization of Thin Titanium and Titanium Nitride Layers Using SIMS

Asymmetrical Heating Behavior at Ni/Doped-Si Junctions for SOI Structures

Oxide Mediated Epitaxy on Planar and Non-Planar Si

Electrochemical and Material Study of Electroless Ternary Barriers for Copper Interconnects

Is Selective CVD an Improvement for the Titanium Silicide Process in Sub-Quarter Micron Technology? A Phase Formation Study Using X-ray Diffraction

The Stability of Aging of Pd/Zn and Pt-Based Ohmic Contacts to p-InGaAs/InP

Metal-GaN Contact Technology

Metal Contact on Nitride-Based Materials

Growth and Characterization of Rare-Earth Phosphide/Arsenide Schottky Contacts to GaAs

In-Situ Regrowth of GaAs Through Controlled Phase Transformations and Reactions of Thin Films on GaAs

Epitaxial Growth of CoGa on (100)GaAs by Metal-Organic Molecular Beam Epitaxy

High-Resolution Auger Imaging Combined with Focused Ion Beam for the Investigation of Metal/GaAs Contacts in High-Power Transistors

Carbon Nanotubes: Molecular Electronic Devices and Interconnects

Organically Deposited Metallic Films for Device Fabrication

Conducting Thin Films of Ruthenium Oxide Prepared by MOCVD

Self-Aligned Gate Metallization Processes With Low-Thermal Budget

Processing of Pure Ni MOCVD Films

Low-Temperature CVD Route to Binary and Ternary Diffusion Barrier Nitrides for Cu Metallization

The Best Way to Obtain Good Quality CVD-TiN Films From TiCl$_4$ and NH$_3$[superscript 3]

Development of a Titanium Nitride Thin Film Standard

Novel Diffusion Barrier with Ultra-Thin Silicon Nitride Cap Layer
PVD Ti-Si-N Films Process Development for Copper Interconnect Applications p. 513
Ultra-Thin TaN Films as Diffusion Barriers for Cu Metallization p. 521
Effect of NH$_3$ Plasma Treatment on Etching of Ti During TiCl$_4$-Based TiN CVD Processes p. 523
Chemical Vapor Deposition of Tantalum Nitride Films Using Pentakis(diethylamido)tantalum and Ammonia p. 531
Copper Metallization Layers on Bismuth-Telluride Substrates: Effectiveness of Cr, Pt, and Ta$_{40}$Si$_{14}$N$_{46}$ Thin Films As Diffusion Barriers p. 537
Optimizing Sputtered TiN Arc Film Properties for Lithography of Sub-0.25 [mu]m Interconnect p. 539
Interfacial Reactions in Multilayers Intended for Microelectronics Devices p. 547
Author Index p. 553
Subject Index p. 557
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